Electronic Band Structure and Kondo Coupling in YbRh₂Si₂

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(Dated: March 22, 2007)

The electronic band structure of YbRh₂Si₂ is calculated in a relativistic framework including correlation corrections and magnetization of the Yb ion and compared to detailed angle-resolved photoemission spectra. The photoemission spectra for LuRh₂Si₂ are used as reference to identify electronic bands with no-f symmetry. The calculated band structure manifests a $4f^{13}$ spin-polarized configuration leaving the unoccupied state at 1.4 eV above the Fermi energy. At the band theory level, the 4f bands are located far below the Fermi level and the anisotropic Coulomb interaction within the 4f shell spreads the multilevel into broader 4f complexes below -2.5 eV. The photoemission spectra obtained on YbRh₂Si₂ show a clear f-multilevel splitting into j = 7/2 and 5/2 excitations. The interaction of the $4f_{7/2}$ -levels close to the Fermi energy with two conduction bands shows visible hybridization gaps of 45 meV and 80 meV, respectively. We discuss the origin of these excitations and provide an analysis according to Anderson's single impurity model with parameters suggested by the band structure calculation and the photoemission spectra. Both experiment and theory indicate nearly identical Fermi surfaces for LuRh₂Si₂ and YbRh₂Si₂. The valency of Yb in YbRh₂Si₂ is estimated to be close to +3.

PACS numbers: 71.20.-b, 79.60.-i, 75.20.Hr

I. INTRODUCTION

Heavy fermion (HF) systems on the border of a zerotemperature magnetic transition have been particularly attractive in the past years [1] because of their anomalous low-temperature thermodynamic, transport and magnetic properties that deviate strongly from Landau Fermi Liquid (LFL) theory. Recently, an increasing number of examples of Ce and U based systems such as $CeCu_{6-x}Au_x$, $CePd_2Si_2$, $CeIn_3$ and U_2Pt_2In have been found to exhibit magnetic quantum criticality by either doping- or pressure-tuning. [2–5] $\rm YbRh_2Si_2$ has attracted attention as the first observed Yb-based and stoichiometric HF system with competing Kondo and Ruderman-Kittel-Kasuya-Yosida (RKKY) interaction, i.e. the dominant exchange mechanisms in metals where the moments interact through the intermediary conduction electrons [6, 7]. Indeed, in YbRh₂Si₂, a very weak antiferromagnetic (AFM) order with a tiny magnetic moment of $\mu_{Yb} \approx (10^{-2} - 10^{-3})\mu_B$ [8] is observed at ambient pressure below the Néel temperature $T_N \simeq 70$ mK. Pronounced non-Fermi Liquid (NFL) behavior has been observed in the resistivity $\rho(T)$ and the electronic specific heat $\Delta C(T)$ at low temperatures showing $\Delta \rho$ = $\rho - \rho_0 \propto T$ and $\Delta C/T \propto - \ln(T)$, respectively.[9, 10] The ground state properties of YbRh₂Si₂ can be easily tuned around the magnetic quantum critical point (QCP) by control parameters such as pressure, magnetic field or doping.[1] An external pressure compresses the atomic lattice leading to an increase of the antiferromagnetic coupling with a maximal Néel temperature of 1 K at 2.7 GPa.[9, 11] On the other hand, expanding the lattice by replacing Si by Ge [12] or Yb by La favors the Kondo coupling and reduces T_N . Approximately 5% Ge- or La-doping completely destroys the antiferromagnetic order in YbRh₂Si₂. Electron spin resonance (ESR) and nuclear magnetic resonance (NMR) experiments have demonstrated the importance of magnetic fluctuations at low T.[8, 13] At intermediate temperatures, a regime emerges for which it is believed that the quantum critical fluctuations dominate and the notion of a well defined quasiparticle breaks down. Remarkably, in YbRh₂Si₂ this regime extends up to 10 K.[10]

A Hall effect measurement suggested a discontinuity in the Fermi surface (FS) volume of 1 charge carrier across the quantum phase transition. [14] Based on a local density approximation (LDA) calculation, the change in the FS volume by unit charge was suggested to arise from a shift of the f-levels across a quantum transition from the antiferromagnetic phase to the Kondo Fermi liquid.[15] Concurring theories on critical heavy fermi liquids assume f-electrons to be partly integrated into a large Fermi surface (FS), and distinguish between visible quasiparticle peaks (SDW case) versus a vanishing Kondo resonance.[16] A direct measurement of the electronic band structure and especially the location and renormalization of f-derived electronic bands, their hybridization with the conduction bands and their incorporation into the FS could provide a stringent test of such theories. Angle-resolved photoemission spectroscopy (ARPES) has proven to be uniquely powerful in its capability to directly probe the electronic structure of solids.[17]

We report here the first band structure calculations reflecting the Yb³⁺ ion that is observed by macroscopic experiments at elevated temperatures. Previous calculations have only modeled a nonmagnetic Yb²⁺ ion.



FIG. 1: (Color online) Crystal structure of YbRh₂Si₂.

We compare the angle-resolved photoemission spectra for YbRh₂Si₂ in the ordinary Kondo-screened state with those for LuRh₂Si₂. The comparison of the Yb and Lu compounds provides a definitive identification of the 4f derived states in the Yb compound. Most importantly, we have directly observed evidence of hybridization between the 4f state and valence states, yielding hybridization gaps ranging from 30 to 80 meV. We performed an analysis of the 4f-derived spectrum $\rho_{\nu}(\epsilon)$ within the single-impurity Anderson model (SIAM) [18] using parameters suggested by the band structure calculation, which leads to a picture that differs from those presented in previous studies. This analysis explains $\rho_{\nu}(\epsilon)$ and macroscopic parameters such as the Kondo temperature T_K in reasonable agreement with the experiments.

II. ELECTRONIC STRUCTURE CALCULATIONS

A. Structure

The crystal structure of YbRh₂Si₂, displayed in Fig. 1, is bct with I4/mmm space group (No. 139). The Yb ion occupies the 2*a* site which has full tetragonal 4/mmm symmetry and forms a bct sublattice, which becomes important in the interpretation of its magnetic behavior. Rh resides in a 4*d* site ($\bar{4}m2$ symmetry), and lie on a simple tetragonal sublattice rotated by 45° in the plane and having lattice constants $a/\sqrt{2}$ and c/2. Si is in the 4e site (4mm); the Si-Si interatomic distances 2.46 Å is only 5% longer than in diamond structure Si, so one view of

the structure is in terms of Si₂ dimers oriented along the \hat{z} axis. Yb atoms and the dimers form a centered square lattice in the x - y plane. Yb is eightfold coordinated by Rh at a distance of 3.17 Å. The atomic positions are [in units of (a, a, c)]: Yb (0,0,0), Rh $(0,\frac{1}{2},\frac{1}{4})$, Si (0,0,0.375); note that the Si height is not determined by symmetry and is accidentally equal to $\frac{3}{8}$. The experimental lattice constants a = 4.010 Å and c = 9.841 Å have been used in our calculations.

For reference, we have also calculated the band structure of isostructural and isovalent LuRh₂Si₂ (a=4.090 Å, c= 10.18 Å). In this compound Lu has a filled 4f shell under all conditions and the compound is a conventional nonmagnetic metallic Fermi liquid.

B. Methods

Rare earth atoms, and other atoms with strong effective intraatomic Coulomb repulsion U (Hubbard U) pose a serious challenge for band theoretical methods. Density functional theory addresses at the most basic level the ground state, which gives the Hund's rule ground state of the Yb ion a central role. Hund's rule implies that one leaves consideration of spin-orbit coupling (SOC) until after the spin S and angular momentum L have been maximized. On the other hand, for interpreting singleparticle-like excitations, which is the main topic of this paper, one wants to obtain the $j = \ell \pm \frac{1}{2}$ character of the excitations. Thus one must include SOC at the oneelectron level, and that is the viewpoint that we take here. From the Curie-Weiss susceptibility at high temperature in $YbRh_2Si_2$ it is clear that the Yb ion is primarily in an $4f^{13}$ configuration (at elevated temperature, at least), corresponding to $S = \frac{1}{2}$, L = 3, $J = \frac{7}{2}$ in the absence of crystal fields.

To be able to include the necessary combination of exchange splitting (magnetic order), SOC, and also the local density approximation plus intraatomic repulsion U (LDA+U) approach that is necessary for rare earth atoms, we have used the Wien2k electronic structure code. [19] An f^{13} configuration necessarily requires a magnetic ion, and we consider only the simplest (ferromagnetic) alignment of Yb spins. With magnetization along (001) direction, SOC reduces the symmetry to Abm2(#39). The around-mean-field version of LDA+U (appropriate for small spin) was used, with U = 8 eV, J=1eV. In the results presented below, the m=0.4f orbital was unoccupied. We have also obtained a solution with the m=-2 orbital unoccupied. (The Hund's rule state would have m=+3 unoccupied.) There is no difference in the results that are discussed here, only minor differences in the placement of the Yb 4f bands. The filled f^{14} shell of Lu does not present any of these complications. To obtain an accurate determination of the Fermi surface we have used a k mesh of 20^3 (641 k-points in the IBZ), $R K_{max}=9$, and the Perdew-Burke-Ernzerhof generalized gradient approximation[20] for exchange correlation potential. An energy range from -7 Ry to 7 Ry is used when SOC is incorporated.

C. Band Structure Results

The band structure of YbRh₂Si₂ shown in Fig. 2 is characterized by the expected $4f^{13}$ spin-polarized configuration of the Yb ion. Without SOC this would correspond to one hole in the minority 4f shell. With SOC included, as here, the flat 4f band complex is spin-mixed and split into a $4f_{5/2}$ complex and a $4f_{7/2}$ complex separated by the spin-orbit splitting of roughly 1.3 eV. Although each 4f band is quite flat, each of the complexes of 2j + 1 bands $(j = \frac{5}{2}, \frac{7}{2})$ is split due to the anisotropy of the Coulomb interaction [21] within the 4f shell, which is included fully in the LDA+U method. However, the 4f electrons are polarized (one hole, $S=\frac{1}{2}$) which induces also a Hund's (exchange) splitting that complicates the identification in the figure of the $4f_{5/2}$ and $4f_{7/2}$ states separately. However, the result that is pertinent to this paper is that this electronic structure calculation fully includes magnetic and relativistic effects, and intraatomic correlation in a static but self-consistent manner, and leaves one hole in the 4f shell consistent with the Curie-Weiss susceptibility.

The unoccupied 4f band lies 1.4 eV above the Fermi level E_F and can be seen to mix exceedingly weakly with the itinerant (Rh+Yb+Si) bands, reflecting its very localized character. The occupied levels lie 2.5 eV or more below E_F and also hybridize weakly. Hence at the band structure level the 4f states are well away from the Fermi level. Many body interactions arising through coupling to the conduction bands may of course lead to large renormalizations as reflected in the experimental data (see Sec. I). We focus first on the states near and at E_F , and then return to the (Kondo) coupling of the 4fmoment to the Fermi surfaces.

The total Rh 4d and total Yb 5d characters are shown separately in the projected orbital character representations in Fig. 2. Much of the Rh 4d bands is occupied, while most of the Yb 5d bands is unoccupied; however there is Yb 5d character around and even below the Fermi level. The Si 3p character is spread fairly evenly through the valence and conduction bands. The bands around E_F have mostly Rh 4d character, with some Yb 5d mixed in, and the bands along symmetry lines are clearly associated with certain symmetry-determined irreducible representations $a_g (d_{3z^2-r^2})$, $b_{1g}(d_{x^2-y^2})$, $b_{2g}(d_{xy})$ or $e_g(d_{xz}, d_{yz})$ of the Rh and Yb d states.

The first noteworthy feature is the band lying 0.2 eV below E_F at Γ , which is completely flat along $\Gamma - Z$ $[(0,0,k_z)$ line] and disperses upward in the plane: this is a pure Rh $d_{x^2-y^2}$ band. There is also strong Rh $4d_{x^2-y^2}$ character at -5 eV (within the 4f bands), presumably the bonding combination of $d_{x^2-y^2}$ orbitals on the two Rh atoms in the cell. The Rh $d_{x^2-y^2}$ band crossing E_F contributes the cylindrical faces of the electron-type tall pill-



FIG. 2: Band structure of YbRh₂Si₂ along tetragonal symmetry lines. The cartesian symmetry line indices are $\Gamma(0,0,0)$, X(1,0,0), M(1,1,0), Z(0,0,1), in units of $[\frac{\pi}{a}, \frac{\pi}{a}, \frac{2\pi}{c}]$. Top panel: bands with total Rh 4*d* emphasized using the fatbands representation. Bottom panel: same bands with total Yb 5*d* emphasized using the fatbands representation.



FIG. 3: (Color online) Total and projected (per atom) density of states of YbRh₂Si₂ corresponding to the band structure in Fig. 2. Rh 4d character dominates around the Fermi level.

box \mathcal{P} FS with (near circular) mean radius in the plane of $k_F=0.133~\frac{\pi}{a}$. All three FSs are displayed in Fig. 4. The Fermi level is intersected along $\Gamma - Z$ by a band composed of Rh $4d_{3z^2-r^2}$, Yb $5d_{3z^2-r^2}$ character and 2 eV wide. This band defines the top and bottom faces of the Γ -centered pillbox, with Fermi wavevector $k_F = 0.265\frac{2\pi}{c}$ along the \hat{z} axis. This pillbox contains $\sim 4 \times 10^{-3}$ carriers/formula unit.

From the bands in Fig. 2 it can be observed that a hole-type surface nearly closes at the $X=(\frac{\pi}{a},0,0)$ point. Because the point we call X is not on the bct Brillouin zone boundary (the true zone is shown in Fig. 4), this is not a small ellipsoid as might be guessed, but rather part of tubes of a multiply connected jungle gym surface \mathcal{J} . The largest part of this surface encircles nearly all of the upper zone face centered on the $Z=(0,0,\frac{2\pi}{c})$ point. The character near X is Rh $4d_{xz}, 4d_{yz}$, and some Yb 5d character. There is also strong Rh $4d_{xz}, 4d_{yz}$ character in the flat band along $\Gamma - Z$ near -3 eV. Rh $4d_{xy}$ character dominates the flat band at -1.5 eV along $\Gamma - Z$, which disperses downward from there within the plane.

The other Fermi surface, also shown in Fig. 4, is a fluted donut \mathcal{D} centered at the Z point and oriented in the x-y plane. It arises partially from the upward dispersion in the x-y plane of the band that lies at -30 meV at Z. This donut \mathcal{D} surface contains electrons.

The FS of LuRh₂Si₂ is nearly identical, as anticipated from the identical structures and the isovalence of the rare earth ions. One change occurs due to a small difference in band energy at and near the X point. The \mathcal{J} surface changes its connectivity and shape as a result, but remains a large (and generally similar) FS.

D. Aspects of Kondo Coupling

YbRh₂Si₂ is a heavy fermion compound, whose $J = L + S = \frac{7}{2}$ ion and associated local moment will be affected by crystal fields and finally screened by conduction electrons at low temperature (a tiny moment survives and orders in YbRh₂Si₂; see Sec. I). Thus, while our ferromagnetic state with $S = \frac{1}{2}$ is not expected to describe the interacting ground state, it has the virtue of providing a measure of the degree of Kondo coupling of the Yb moment to the Fermi surfaces, because the exchange splitting of the Fermi surfaces reflects the coupling of the local moment to the itinerant bands.

The exchange splitting of the Γ cylinder is 6 meV around its waist (in the x - y plane) and 30 meV at top and bottom, a strong anisotropy resulting from the different characters of wavefunctions on the different parts of the surface. For points on the \mathcal{J} surface near the X point, the exchange splitting is 20 meV at both $(0.95,0,0)\frac{\pi}{a}$ and $(1,0.2,0)\frac{\pi}{a}$. Thus the Kondo coupling, and likewise the carrier scattering by the moments, differs by at least a factor of five around the Fermi surfaces.

E. Discussion of Bands and Fermi Surfaces

This fully relativistic, spin-polarized LDA+U band structure and resulting Fermi surfaces can be compared with previous unpolarized relativistic LDA prediction.[15, 22, 23] Not surprisingly there are substantial differences, as expected from the LDA's $4f^{14}$ configuration versus our magnetic $4f^{13}$ bands; this difference in Yb 4f charge state puts Norman's Fermi level one electron lower with respect to the Rh 4d + Yb 5d + Si 3pitinerant bands.[15] As a result, the flat Rh $4d_{x^2-y^2}$ band that lies 0.2 eV below \mathbf{E}_F in our bands lies 0.1 eV above \mathbf{E}_F in the LDA bands, and the Fermi surfaces are entirely different. These differences will lead to completely different predictions for the Hall coefficient.

On the qualitative level, our Fermi surfaces include large sheets with cancelling positive and negative contributions to the Hall coefficient, as do Norman's. The Hall coefficient, usually thought of (in the constant relaxation times approximation) as being an average of the Fermi surface curvature, will bear no relation to the number of carriers. No doubt it will be quite anisotropic, given the strong tetragonality of the FSs. The edges of the pillbox \mathcal{P} may give large contributions (and make evaluation difficult); likewise, the sharp edges on the donut \mathcal{D} will also have large curvatures.

The 'curvature' interpretation of the Hall tensor relies on the isotropic scattering time approximation. This situation is unlikely to be the case in YbRh₂Si₂, where the main scattering arises from the Kondo coupling to local moments. As pointed out in the previous subsection, this coupling varies strongly over the Fermi surface (by at least a factor of five). Hence this system is an example of a multiband (correlated) metal with large Fermi sur-



FIG. 4: The three calculated Fermi surfaces of YbRh₂Si₂ with $4f^{13}$ configuration, pictured within the crystallographic Brillouin zone. Top panel: fluted donut \mathcal{D} surface centered around the upper zone face midpoint Z. Middle panel: multiply-connected jungle gym \mathcal{J} surface. Bottom panel: tall pillbox surface \mathcal{P} , containing electrons at the zone center Γ . The Fermi surfaces of LuRh₂Si₂ are very similar; see text.

faces of varying curvature, having large and anisotropic scattering. Its Hall tensor, versus temperature, field, and magnetic ordering, promises to be very challenging to understand.

III. EXPERIMENTS

Millimeter sized single crystalline platelets of $LuRh_2Si_2$ and $YbRh_2Si_2$ were grown by the flux-growth method using an In flux in a sealed Ta tube under argon atmosphere. The crystals were washed in HCl acid solution to safely remove excess In flux. The tetragonal crystal structure and the lattice parameters were confirmed by X-ray powder diffraction.

The ARPES measurements were performed using a chamber equipped with a Scienta SES200 analyzer attached to the undulator beamline 5-4 of Stanford Synchrotron Radiation Laboratory (SSRL) and a second vacuum system equipped with a Scienta SES2002 analyzer and a microwave driven monochromatized He-discharge lamp (Gammadata VUV5000). At SSRL, we used linearly polarized photons of 21.4 eV. The photoemission spectra at these photon energies allow a detailed comparison of the electronic states with no f-symmetry in LuRh₂Si₂ and YbRh₂Si₂. We intentionally refrained from tuning the photon energy to resonance with Ybcore levels which enhances the photoelectron yield of the Yb 4f-electrons but worsens the energy resolution by approximately 6-8 times. At these low energies, the photoelectron mean free path becomes very short and care has to be taken regarding identifying surface and bulk states. Fortunately, there are numerous reports having dealt with this issue in Yb-related materials [24, 26, 27] and also in YbRh₂Si₂. [22] An energy resolution of \sim 40 meV or more hides the relevant hybridization features in the angle-resolved spectra for the critical system YbRh₂Si₂. The total energy resolution including the monochromator and the analyzer was 8 meV for the 21.2 eV beam from the He-source, and 22 meV for the 21.4eV Synchrotron beam, respectively. The chamber pressure was below $4 \cdot 10^{-11}$ torr. The samples were cleaved in situ at $T \sim 14$ K. As opposed to previous experiments on Yb- or Ce-based material, very clean cleaves with large flat greyish-shiny areas can be obtained on these 1-2-2 compounds where the electronic spectra manifest sharp features. The excellent quality of the surface has been determined using high-resolution LEED. The position of the Fermi level (E_F) was calibrated from the Fermi edge of polycristalline Au for every measurement.

IV. PHOTOEMISSION RESULTS AND DISCUSSION

A. Angle-integrated spectrum at $h\nu = 40.8 \text{ eV}$

Fig. 5 shows the angle-integrated spectrum for YbRh₂Si₂ (red curve) at angles between -5° and 17° in the Γ -M-Z plane measured with He-II radiation. The broad distribution of intensity between -11 and -7.5 eV, indicated by the shaded area in Fig. 5, included emission from Si 3s states, as indicated by the band structure calculations. At low binding energies, we can identify



FIG. 5: (Color online) Angle-integrated PE spectrum (red curve) of $YbRh_2Si_2$ measured with photon energy of 40.8 eV at 14 K. The lines are explained in subsection IV A.

two sharp but small intensity maxima at \sim - 1.3 eV and right at E_F with a peak intensity ratio of approximately 2:3, respectively. The corresponding data for $h\nu = 21.2$ eV do not display any pronounced intensity at these energies. Hence, these are single-hole, very weakly hybridized j = 7/2 and j = 5/2 states split by the 1.3 eV SOC energy (see section IVC). The intense peaks at 650 meV and at 2 eV can be attributed to the spin-orbit split surface bands [28] originating from Yb ions at or close to the sample surface. The relative intensity of surface vs. bulk peaks decreases strongly when the photon energy is increased from 21 to 41 eV and 110 eV. [22] The intensity around 3 eV is not due to flat bands but is a result of various co-terminating band edges having high intensities in that energy region which is seen in the angle-resolved spectrum in Fig. 7. We refer to Ref. [22] where the 4f-intensities can be compared to the atomistic calculations of Gerken [29]. However, this manuscript focuses on the excitations close to the Fermi energy, related to the Yb-4 $f_{7/2}^{13}$ excitations.

B. Angle-resolved spectra for $LuRh_2Si_2$ and $\label{eq:spectra} YbRh_2Si_2$

Within the sudden approximation, [17] angle-resolved photoemission measures the single-particle spectral function $A(k, \omega)$, where k is the crystal momentum and ω is the photohole energy, taken at a beam energy $h\nu = 21.2$ eV. For quasi-2D materials, it is the in plane component of the crystal momentum k_{\parallel} that matters. We will plot



FIG. 6: (Color online) Panel a) and b): angle-resolved PE spectra for LuRh₂Si₂ taken in our case at 21.2 eV in the $\tilde{\Gamma}\tilde{M}$ direction. The numbers are referred to in the text. Panel c): angle-resolved spectrum of LuRh₂Si₂ in the $\tilde{\Gamma}\tilde{X}$ direction. Panel d): EDC plot for the ΓM direction near $\tilde{\Gamma}$.

the data with respect to k_{\parallel} , however we note that the 3D behavior can be important in this material. $\tilde{\Gamma}$, \tilde{M} , \tilde{X} and \tilde{Z} refer to locations in the BZ close to the Γ , M, X and Z points in the real BZ, respectively. The threedimensional nature of the bands, and hence of the photoemission process, inhibits more precise identification in k-space (i.e. of k_z). The distance $\tilde{\Gamma}\tilde{X}$ is approximately equivalent to ΓX in the center of the Brillouin zone (BZ). In order to connect to the calculations, we use ω , ϵ and E- E_F on an equal basis in the following discussions.

At the most rudimentary level, LuRh₂Si₂ and YbRh₂Si₂ differ only by one electron in the 4*f*-shell on the rare-earth ion. Whereas high-temperature experiments have shown that in these materials, Yb is in the magnetic $4f^{13}$ state, Lu has a filled shell and the 4*f*electron levels are expected to be at elevated binding energies. Hence, comparing photoemission results for these compounds can yield insight into the nature of the various electronic bands with no-f symmetry.

 $LuRh_2Si_2$. The top two plots of Fig. 6 show the angleresolved photoemission spectra for LuRh₂Si₂ in the $\tilde{\Gamma}$ -M-Z-plane with different energy scales measured at 21.2 eV. Comparing the EDC and the FS images to the results of the band structure calculations we conclude that Γ lies on a point slightly below 1/4 of the line from -Z to $\Gamma.\,$ Several bands - 1, 2, 3, 4 and 5 - cross the Fermi level and form Fermi surfaces. Since the LDA calculation for LuRh₂Si₂ yields nearly the identical FS as the LDA+U+SOC calculation does for YbRh₂Si₂ these sheets can be compared to the corresponding ones in Fig. 4. Bands 4 and 5 are already in the neighboring BZ. They can be ascribed to the donut-shaped \mathcal{D} and jungle-gym \mathcal{J} FSs, respectively. Band 1, i.e. the Rh-4d band, shows a parabolic dispersion where the spectral weight increases strongly as E_F is approached near Γ . The lower right panel of Fig. 6 reveals however, that it is not only a single band but a steep one (band 1) and a flat one, band 1' meeting at $\tilde{\Gamma}$ without opening a clearly detectable hybridization gap.

 $YbRh_2Si_2$. The upper panel of Fig. 7 shows an angleresolved photoemission spectrum in the $\Gamma - X - Z$ -plane measured again at the same 21.2 eV. Compared with the $LuRh_2Si_2$, we have evidence for four additional bands between E_F and 2 eV binding energy, suggesting that these are Yb derived 4f states, an assignment consistent with these bands being extremely flat. Two different flat bands display a pronounced intensity, band (fb_1) located very close to E_F , and band (fs_1) with a maximum intensity at $\approx 680 \text{ meV}$ below E_F . The latter derives from electronic states of Yb atoms close to the sample surface (see subsection IVA). Previous spectroscopic experiments [30] and fully relativistic calculations (see Fig. 2) revealed that the spin-orbit interaction in Yb-based materials is of the order of 1.3 eV, consistent with the value obtained within the relativistic calculation (see section II).

Masked in the primary spectra by the high intensity of neighboring bands, the second derivative plot (lower panel of Fig. 7) reveals a third very flat electronic band (fb_2) separated from band (fb_1) by the spin-orbit splitting $\Delta \epsilon_f \approx 1.3$ eV and a fourth flat band (fs_2) 1.3 eV below band (fs_1) , i.e. the bulk and surface $4f_{5/2}^{13}$ final states, respectively. Neither a careful investigation of the spectra nor the second derivative plot revealed an addi-



FIG. 7: (Color online) Angle-resolved PE spectra of YbRh₂Si₂ taken at $h\nu = 21.4$ eV at T = 14 K in the Γ -X-Z plane. The lower panel shows the second derivative of the spectrum (upper panel). The relevant bands are denoted as (fb_1) and (fb_2) for the bulk $4f^{13}$ and (fs_1) and (fs_2) for the surface $4f^{13}$ states, P_1 and P_2 are valence bands with mostly Rh-4d-and partly Yb-5d-character for the latter one.

tional flat band with f-symmetry as indicated by the LDA+U+SOC band structure calculation. This observation reflects the fact that the LDA+U eigenvalues are not in one-to-one correspondence with photohole energies in open strongly correlated shells, and more especially so when there is important coupling to valence states as is clearly the case in YbRh₂Si₂. Hence, the f-excitations are split into a $4f_{5/2}$ peak at \sim -1.3 eV and a sharp band of 4f-electrons with j = 7/2 centered at \sim -45 meV with

a peak width of $\Gamma_{FWHM} \approx 30$ meV obtained from an EDC-fit to a Lorentzian shape.

A strong intensity is displayed by the band (P_1) which shows nearly a free electron parabola with band width Bdown to -3.6 eV at the X-point and nearly 6 eV at the M-point (see lower left panel in Fig. 6). While the band consists of several overlapping components, comparison with LDA+U band structure suggests that it is mostly states of Rh-4d character. While the real band structure is more complicated, we will use a nearly-free parabola to mimic this band for continuation $\epsilon > 0$ eV and simulating the 4f spectral weight later. Moreover, band (P_1) also crosses and mixes with the Yb-derived surface bands (fs_1) and (fs_2) around Γ . Since the Si-ions form strongly bonded Si₂-dimers that encage the Yb-ions, the first Yblayer is intermediate between a bulk and a surface layer such that it can be distorted by hybridization with a bulk band.

Half-way between the Γ and the X point, a band (P_2) , displaying a very weak intensity, hybridizes with the fband. We will show in Fig. 8 how this hybridization arises. This band P_2 starts at approximately -2 eV close to M and crosses E_F near X as observed in Fig. 2. Considering the wave-function symmetry of this band, it can be continued in a nearly-free parabola to approximately 2 eV above E_F at Γ . This band induces the hole-like FS \mathcal{D} . At ~ 20-25 angular degrees, we observe two different bands denoted as (d_1) and (d_2) . They form the jungle gym FS sheet \mathcal{J} and will be briefly discussed in the subsection IV D.

The upper left panel of Fig. 8 shows $A(k_{\parallel}, \omega)$ measured in the vicinity of $\tilde{\Gamma}$ using a photon energy of 21.2 eV. At very small angles, the $4f_{7/2}$ -band (fb_1) with peak width less than 35 meV hybridizes weakly with the Rh 4dband leading to a dispersion of ≈ 10 meV. A gap between the peaks of the two bands of approximately 80 meV is observed. For $\omega \geq -20$ meV, $A(k_{\parallel}, \omega)$ rises again towards lower binding energies indicating a double peak structure. In analogy to the spectra for $LuRh_2Si_2$, we observe a similar double peak structure between two dispersing Rh-bands, but now they are separated by an Yb-f band. Nearly no dispersion is observed for the peak below 20 meV binding energy. We note here, that this feature near E_F does not follow the dispersion behavior of the f-band, but it is rather limited to a small region around Γ . Furthermore, as we change the photon energy between 17 eV and 31 eV, the intensity at E_F remains almost unchanged (not shown here), characteristic for a band with minimal dispersion in the k_z -direction. Hence, this lowest energy peak at Γ cannot be considered as a candidate for the Kondo resonance as it has a correspondent component in $LuRh_2Si_2$.

Panels (C) and (D) of Fig. 8 show a photoemission spectrum along the yellow line in Fig. 9. The top-right panel shows the raw data, the bottom right is the corresponding EDC data. The red circles are obtained by fitting a single Lorentzian and a constant background to the EDC curves and the blue thick line sets the Fermi level. A steep band (band (P_2) in Fig. 7) with strong Rh-*d* character hybridizes with the flat Yb *f*-band. This induces an opening of a band gap of the order of 30-40 meV. We note that this gap is too small to incorporate significant *f*-spectral weight into the FS.

C. The 4*f*-excitation spectrum

Now we now come back to the 4f states. As in [22], there is complex 4f spectral weight for binding energies above 4 eV, consistent with the LDA+U+SOC calculation in Fig. 2. Unlike band theory, we observe two 4fderived bulk features between E_F and -1.3 eV, arising from many body interactions. They are usually related to $4f_{7/2}$ - and $4f_{5/2}$ -excitations and denoted as the Kondo resonance and its spin-orbit side band.[24, 25] The additional splitting due to an anisotropic Coulomb interaction that would lead to distinct energies of different l = 3 hole orbitals is not observed.

We have performed a Gunnarsson-Schönhammer (GS) [25] analysis using parameters suggested by the band structure calculations which differ significantly from those normally used in the literature. [24–26, 31] This scheme employs a second-order perturbative calculation based on the Anderson single-impurity model. We will assume $U = \infty$ and a large SOC in order to study only the $4f_{7/2}^{13}$ states with degeneracy $N_f = 8$.

As is usual in GS calculations, we model the valence band with a semielliptical density of states, in our case extending from -6 to 6 eV. Based on our earlier discussion, we represent the P_2 band with a half-filled semielliptical form ranging from -1.8 to 2.4 eV. The hybridization strength V is related to the gap Δ by $\Delta = 2V^2/B$, where B is the bandwidth of the related conduction band. The solution for the spectrum is equivalent to the solution for the BIS spectrum in cerium material, replacing the electrons by holes and inserting the form for the valence bands obtained from the band structure calculations. The electronic gaps in the photoemission spectra are given for the interaction with parabola (P_1) as $\Delta_1 \sim$ 80 meV observed in panel (A) of Fig. 8 and for the interaction with parabola (P_2) as $\Delta_2 \sim 45$ meV observed in the panels (C) and (D) of Fig. 8. In order to reproduce the spectrum we vary ϵ_f , the 8-fold degenerate f-level.

The spectrum (open symbols in panel (B) of Fig. 8) is obtained by integrating the angle-resolved photoemission data between 0° and 20° at 21.2 eV and subtracting the contribution from the Rh-4d band using a Doniach-Sunjic lineshape.[32] Furthermore, we subtracted the intensity from the $4f_{5/2}$ surface state centered at 2 eV using a Lorentzian and a uniform background as in Ref. [24]. The subtraction is rather tedious and perfect agreement with the calculation cannot be expected. The features of interest are two strong intensity regions, one centered at -1.35 eV and at -45 meV with intensity ratios of 2:3. The peak at -1.35 eV which mimics the $4f_{5/2}$ excitation is approximated by a Lorentzian with line width ~ 55



FIG. 8: (Color online) Panel (A): experimental PE spectrum for small energies in the vicinity of $\tilde{\Gamma}$. Panel (B): The empty circles represent the spectrum solely due to the 4f final states obtained as explained in the text. The solid red line is a calculation according the GS-scheme explained in the text. The long-dashed line is a Lorentzian to the surface peak. The right panels show the hybridization of the f-band with the band (P₂). Panels (C) and (D) show the spectrum where band (P₂) and (fb₁) hybridize. The zero in the Δk -axis denotes the wave vector $k_{\parallel} = 0.385 \cdot \Gamma X \cdot (0.985, 0.174)$ and we measure along the yellow line in Fig. 9.

meV where we subtracted the background. As noted earlier, the feature at -0.7 eV is due to a surface state. Its emission is approximated by a Lorentzian with line width ~ 230 meV (see black dashed line). The feature at higher binding energy is slightly asymmetric, and some additional intensity around -1.1 eV could not be removed properly.

The result of the GS simulation is shown as a red solid line in panel B) of Fig. 8. The simulation yields an energy $\epsilon_f \approx -1.4 \text{ eV}$ and a hole concentration of 0.99 in the $4f^{14}$ shell, i.e. the full Yb-3+ moment. The asymmetry of the peak at 50 meV can be explained by the arguments of Doniach and Sunjic. [32]

In the spin-fluctuation limit with the f-level occupancy very close to 1, an estimate for the Kondo temperature can be obtained in the GS-scheme [25] as

$$T_K \equiv \delta/k_B = \frac{|\epsilon_f| - \Delta E}{k_B} \approx 30K \quad , \tag{1}$$

where k_B is the Boltzmann constant. The energy gain

through the hybridization is given as

$$\Delta E = N_f \left(\sum_i \int \frac{|V_i(\epsilon)|^2}{\Delta E - \epsilon_f - \epsilon} d\epsilon \right) \quad . \tag{2}$$

The hybridization is determined as $|V_i(\epsilon)|^2 = \Delta_i \sqrt{B_i^2 - \epsilon^2}/B_i$. Kondo temperatures obtained with this method yield only an approximate Kondo scale. However, a Kondo temperature of a few tens of Kelvin is corroborated by the results from macroscopic experiments which yielded $T_K \approx 24$ K. [9, 10]

Previous band structure calculations [15, 28] resulted in the $4f^{14}$ ground state for the Yb-ion. This leads to $4f_{7/2}$ -electronic states at 100-200 meV and $4f_{5/2}$ states at 1.3 eV below E_F . [15, 34] Taken literally, one is tempted to say that this provides an alternative interpretation for the 4f peaks at E_F and at -1.3 eV. With this background, the origin of a peak at 1.3 eV needs further clarification. We also recall that the GS-scheme considers the emission from a mixture of $4f^{13}$ and $4f^{14}$ orbitals and neglects the true many-body essence of the Kondo-resonance. With this in mind, the interpretation of the 4 f-peaks near E_F and 1.3 eV is not straightforward anymore and raises severe doubts if an analysis according the GS-scheme is justified. The interpretation of these two peaks is likely to be given, in an atomistic framework, by Gerken [29] and which has been used for SmB₆ and sometimes also for Yb-related material. [35, 36] In this case, the valency is reduced to approximately +2.9 [22] which however interferes with macroscopic experiments.[9] Given the serious deficiency of recent band structure calculations in getting the correct experimental picture for the Yb-4 f^{13} ion which is then progressively screened at low temperature due to the Kondo effect, and given our GS-scheme simulation which provides a reasonable electronic spectrum and T_K , in balance we favor the Kondo resonance interpretation. We expect time-dependent 2-photon photoemission spectroscopy and DMFT-calculations on pure Yb to yield more information on the nature of these peaks.

We address the recent claim of YbRh₂Si₂ being a mixed valent.[15, 22] If a d-band crosses the *f*-spectrum and the Fermi energy overlaps the *f*-configurational levels to within the hybridization energy, we have a mixed valence compound, i.e. the Yb ions occur both as Yb³⁺ with electronic $4f^{13}$ configuration or Yb²⁺ with $4f^{14}$ configuration. The panels (C) and (D) in Fig. 8 however display that the hybridization energy is smaller than the distance to the Fermi level, i.e. 50 meV, and hence the valency is close to +3.

D. Constant Energy Cuts at 21.2 eV

The results of our band structure calculations suggest that the FS of $LuRh_2Si_2$ does not deviate significantly from the one of YbRh_2Si_2, plotted in Fig. 4.

The lower panel of Fig. 9 shows a FS map of $LuRh_2Si_2$ obtained at a photon energy of 21.2 eV. We integrated



FIG. 9: In the lower panel we plotted a Fermi surface map for LuRh₂Si₂ taken at 21.2 eV. The upper panel shows the corresponding map for YbRh₂Si₂. \mathcal{J}' , \mathcal{D} and \mathcal{J} are three different FS parts as discussed in the text. The dashed line indicates $\frac{\pi}{a}$, where *a* is the length of the lattice bases. Units are given in $\frac{\pi}{a}$.

the intensity over an energy window of 2 meV at E_F . This integration window is extremely narrow. It is imposed by the comparison to the FS of YbRh₂Si₂ where the intensity of the $4f_{7/2}$ excitations appears close to the Fermi level and might falsify the intensity pattern. We distinguish clearly 3 different regions. Right in the center of the BZ we observe a bright intensity \mathcal{J}' which according section IV B is the inner part of the complex jungle-gym sheet forming a tip-like structure. \mathcal{D} is a cut through the donut-like FS sheet centered around the Zpoint of the BZ. Its intensity is blurred out because of considerable k_z -dispersion. \mathcal{J} is again a cut through the complex jungle-gym sheet at the border of the BZ. For a better understanding compare to Fig. 4.

The upper panel of Fig. 9 shows a FS map of YbRh₂Si₂

obtained at the same photon energy of 21.2 eV. We again integrated the intensity over an energy window of 2 meV centered at the Fermi level determined on the gold reference sample. In accordance with the LDA+U+SOC calculations, the FS splits again into three different parts. At Γ , there is a small tip-like area \mathcal{J}' with a high intensity. At the boundary of the BZ the very distinct arms of the FS sheet \mathcal{J} show strong intensities. As indicated by the cut along ΓX in Fig. 7, it appears that for some particular crystal momenta the sheet \mathcal{J} splits into two parts which have been labelled (d_1) and (d_2) , respectively. An MDC/EDC analysis reveals that these excitations have a relatively light effective mass of $m_{eff} \approx 1.2 m_e$. The intensity pattern labelled \mathcal{D} shows a cut through the FS displaying Rh-4d and Yb-5d character and forming the same donut-shaped sheet as observed in LuRh₂Si₂.

We observe that at least qualitatively the Fermi surfaces of LuRh₂Si₂ and YbRh₂Si₂ agree. This confirms the results of the band structure investigations which obtained nearly identical FS for both materials. Hence, we conclude that the Yb-4f electrons contribution to actively forming the FS is small at 14 K.

V. CONCLUSIONS

In this article we have presented the results of an electronic band structure calculation within a relativistic framework including correlation corrections for YbRh₂Si₂. Characteristic of the electronic structure is the $4f^{13}$ ground state as required by the Curie-Weiss moment that is observed at high temperature. A small FS cylinder of $4d_{x^2-y^2}$ -symmetry is centered at Γ , a fluted donut \mathcal{D} surface situated around the upper zone face midpoint Z and a multiply-connected jungle gym \mathcal{J} surface. The angle-resolved photoemission spectrum manifests (true many-body) intensities originating from $4f_{7/2}^{13}$ and $4f_{5/2}^{13}$ final state excitations separated by 1.3 eV, the value for the spin-orbit interaction obtained from the calculation. These excitations are 8- resp. 6-fold degenerate and do not manifest the splitting due to the anisotropic Coulomb interaction inherent to the single-particle energy states.

An analysis of the 4f-spectrum $\rho_{\nu}(\epsilon)$ according the degenerate Anderson impurity model using the parameters obtained from the band structure calculations explains the appearance of a peak related to the $4f_{7/2}$ excitations at 45 meV below E_F . The Kondo splittings obtained from the band structure calculations can be compared to the electronic gaps in the photoemission spectra. In a GS-framework the splitting are $V(\epsilon_F) = V/\pi \approx 33$ meV at Γ and ≈ 16 meV at the BZ boundaries. These values agree with those obtained from the LDA+U+SOC calculation. The Kondo temperature $T_K \sim 30$ K and full Yb-3+ moment are in agreement with the results from macroscopic experiments.

The band structure and FS of LuRh₂Si₂ and YbRh₂Si₂ are compared. The absence of very flat bands in the

Lu compound provides confirmation for the 4f nature of these bands in the Yb compound. Both compounds show very similar Fermi surface features. At the center of the BZ we cut a tip-like sheet which is part of the junglegym FS J. The same sheet is visible with high intensity embracing the X-point of the BZ. Additionally, at 21.2 eV, we observe a large surface centered at the Z-point of the BZ in the form of a donut. There is no clear difference between the FS of both materials observed, neither theoretically nor experimentally. This indicates that the spectral weight of the 4f-bands do not contribute significantly in forming the FS at 14 K.

VI. ACKNOWLEDGEMENT

This work has benefited from partial financial support of the Schweizerische Nationalfonds zur Förderung

- [1] G.R. Stewart, Rev. Mod. Phys. **73**, 797 (2001).
- [2] B. Bogenberger and H. v. Lohneysen, Phys. Rev. Lett. 74, 1016 (1995).
- [3] F.M. Grosche, S.R. Julian, N.D. Mathur, and G.G. Lonzarich, Physica B, **223-224**, 50 (1996).
- [4] I.R. Walker, F.M. Grosche, D.M. Freye, and G.G. Lonzarich, Physica C, 282-287, 303 (1997).
- [5] P. Estrella, A. de Visser, F.R. de Boer, G.J. Nieuwenhuys, L.C.J. Pereira and M. Almeida, Physica B 259-261 409 (1999).
- [6] J. Kondo, Prog. Theor. Physics **32**, 37 (1964).
- [7] M.A. Ruderman and C. Kittel, Phys. Rev. **96**, 99 (1954).
- [8] K. Ishida, D.E. MacLaughlin, O.O. Bernal, R.H. Heffner, G.J. Nieuwenhuys, O. Trovarelli, C. Geibel and F. Steglich Physica B **326**, 403 (2003).
- [9] O. Trovarelli, C. Geibel, S. Mederle, C. Langhammer, F.M. Grosche, P. Gegenwart, M. Lang, G. Sparn, and F. Steglich, Phys. Rev. Lett. 85, 626 (2000).
- [10] P. Gegenwart, J. Custers, C. Geibel, K. Neumaier, T. Tayama, K. Tenya, O. Trovarelli, and F. Steglich, Phys. Rev. Lett. 89, 056402 (2002).
- [11] O. Trovarelli, J. Custers, P. Gegenwart, C. Geibel, P. Hinze, S. Mederle, G. Sparn and F. Steglich, Physica B 312-313, 401 (2002).
- [12] J. Custers, P. Gegenwart, H. Wilhelm, K. Neumaler, Y. Tokiwa, O. Trovarelli, C. Geibel, F. Steglich, C. Pépin and P. Coleman, Nature 424, 524 (2003).
- [13] K. Ishida, K. Okamoto, Y. Kawasaki, Y. Kitaoka, O. Trovarelli, C. Geibel, and F. Steglich Phys. Rev. Lett. 89, 107202 (2002).
- [14] S. Paschen, T. Luhmann, S. Wirth, P. Gegenwart, O. Trovarelli, C. Geibel, F. Steglich, P. Coleman, Q. Si, Nature 432, 881 (2004).
- [15] M.R. Norman, Phys. Rev. B **71**, 220405 (2005).
- [16] Q. Si, S. Rabello, K. Ingersent, J.L. Smith, Phys. Rev. B 68, 115103 (2003).
 [17] G. Witten, Phys. Rev. B (1997) (1997).
- [17] S. Hüfner, *Photoelectron Spectroscopy* (Springer Verlag, Berlin, 1995).
- [18] P.W. Anderson, Phys. Rev. **124**, 41 (1961).

- [19] K. Schwarz, P. Blaha and G. K. H. Madsen, Comput.
- Phys. Commun. 147. 71 (2002). [20] J. P. Perdew, K. Burke, and M. Ernzerhof, Phys. Rev.
- Lett. **77**, 3865 (1996). [21] M.D. Johannes and W.E. Pickett, Phys. Rev. B **72**,
- 195116 (2005).
 [22] S. Danzenbcher, Y. Kucherenko, D.V. Vyalikh, M.
- [22] S. Danzenbener, T. Kucherenko, D.V. Vyanki, M. Holder, C. Laubschat, A.N. Yaresko, C. Krellner, Z. Hossain, C. Geibel, X.J. Zhou, W.L. Yang, N. Mannella, Z. Hussain, Z.-X. Shen, M. Shi, L. Patthey and S.L. Molodtsov, Phys. Rev. B **75**, 045109 (2007).
- [23] for other examples consider: K. Takegahara and Y. Kaneta, J. Phys. Soc. of Japan **60**, 4009 (1991), or I.I. Mazin and L.S. Molodtsov, Phys. Rev. B **72**, 172504 (2005).
- [24] F. Patthey, J.-M. Imer, W.-D. Schneider, H. Beck, Y. Baer and B. Delley, Phys. Rev. B 42, 8864 (1990).
- [25] O. Gunnarsson and K. Schönhammer, Phys. Rev. B 28, 4315 (1983).
- [26] J.W. Allen, S.-J. Oh, I. Lindau, J.M. Lawrence, L.I. Johansson and S.B. Hagström, Phys. Rev. Lett. 81, 1100 (1981); J.W. Allen, G.H. Gweon, H.T. Schek, L.Z. Liu, L.H. Tjeng, J.H. Park, W.P. Wllis, C.T. Chen, O. Gunnarsson, O. Jepsen, O.K. Andersen, Y. Dalichaouch, J. Appl. Phys. 87, 6088 (2000).
- [27] S. Suga, A. Sekiyama, S. Imada, A. Shigemoto, A. Yamasaki, M. Tsunekawa, C. Dallera, L. Braicovich, T.-L. Lee, O. Sakai, T. Ebihara and Y. Onuki, J. Phys. Soc. Japan 74, 2880 (2005).
- [28] S. Danzenbächer, Y. Kucherenko, C. Laubschat, D.V. Vyalikh, Z. Hossain, C. Geibel, N. Mannella, X.J. Zhou, W. Yang, Z.-X. Shen and S.L. Molodstov, Phys. Rev. Lett. 96, 106402 (2006).
- [29] F. Gerken, J. Phys. F: Met. Phys 13, 703 (1983).
- [30] L.H. Tjeng, S.-J. Oh, E.-J. Cho, H.-J. Lin, C.T. Chen, G.-H. Gweon, J.-H. Park, J.W. Allen, T. Suzuki, M.S. Makivić and D.L. Cox, Phys. Rev. Lett. **71**, 1419 (1993).
- [31] A. Sekiyama, T. Iwasaki, K. Matsuda, Y. Saitoh, Y. Onuki and S. Suga, Nature 403, 396 (2000).

der wissenschaftlichen Forschung, the US-DOE grant DE-FG03-01ER45876 and the grant NSF-DMR 0433560. W.E.P. acknowledges support and stimulating atmosphere of the Department of Energy's Stewardship Science Academic Alliances Program, and the hospitality of the Alexander von Humboldt Foundation during the latter stages of this work. W.E.P. and Z.P.Y. acknowledge important interactions within DOE's Computational Materials Science Network team studying strongly correlated materials.

- [32] S. Doniach and M. Sunjic: J. Phys. C 3, 285 (1970).
- [33] F.D.M. Haldane, Phys. Rev. Lett. 40, 416 (1978), or J.H. Jefferson, J. Phys. C 10, 3589 (1997).
- [34] G. Knebel, R. Boursier, E. Hassinger, G. Lapertot, P.G. Noklowitz, A. Pourret, B. Salce, J.P. Sanchez, I. Sheikin, P. Bonville, H. Harima and J. Flouquet, J. Phys. Soc. Japan 75, 114709 (2006).
- [35] V.N. Antonov, B.N. Harmon, A.N. Yaresko, Phys. Rev. B 66, 165209 (2002).
- [36] R.I.R. Blyth, J.J. Joyce, A.J. Arko, P.C. Canfield, A.B. Andrews, Z. Fisk, J.D. Thompson and R.J. Bartlett, P. Riseborough, J. Tang and J.M. Lawrence, Phys. Rev. B 48, 9497 (1993).